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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/707,110	11/21/2003	Kun-Hong Chen	12041-US-PA	1109
31561	7590	08/23/2005	EXAMINER	
JIANQ CHYUN INTELLECTUAL PROPERTY OFFICE 7 FLOOR-1, NO. 100 ROOSEVELT ROAD, SECTION 2 TAIPEI, 100 TAIWAN			A, MINH D	
		ART UNIT		PAPER NUMBER
		2821		
DATE MAILED: 08/23/2005				

Please find below and/or attached an Office communication concerning this application or proceeding.

<b>Office Action Summary</b>	<b>Application No.</b>	<b>Applicant(s)</b>
	10/707,110	CHEN, KUN-HONG
	<b>Examiner</b>	<b>Art Unit</b>
	Minh D. A	2821

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

## Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

## Status

1)  Responsive to communication(s) filed on 27 May 2005.

2a)  This action is **FINAL**.                            2b)  This action is non-final.

3)  Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

## **Disposition of Claims**

4)  Claim(s) 1-17 is/are pending in the application.  
4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.

5)  Claim(s) \_\_\_\_\_ is/are allowed.

6)  Claim(s) 1-17 is/are rejected.

7)  Claim(s) \_\_\_\_\_ is/are objected to.

8)  Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

## Application Papers

9)  The specification is objected to by the Examiner.

10)  The drawing(s) filed on \_\_\_\_\_ is/are: a)  accepted or b)  objected to by the Examiner.

Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11)  The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

**Priority under 35 U.S.C. § 119**

12)  Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
a)  All b)  Some \* c)  None of:  
1.  Certified copies of the priority documents have been received.  
2.  Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
3.  Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

**Attachment(s)**

1)  Notice of References Cited (PTO-892)  
2)  Notice of Draftsperson's Patent Drawing Review (PTO-948)  
3)  Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  
Paper No(s)/Mail Date .  
4)  Interview Summary (PTO-413)  
Paper No(s)/Mail Date. \_\_\_\_ .  
5)  Notice of Informal Patent Application (PTO-152)  
6)  Other: \_\_\_\_ .

## DETAILED ACTION

### ***Claim Rejections - 35 USC § 102***

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) and the Intellectual Property and High Technology Technical Amendments Act of 2002 do not apply when the reference is a U.S. patent resulting directly or indirectly from an international application filed before November 29, 2000. Therefore, the prior art date of the reference is determined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

Claims 1-17 are rejected under 35 U.S.C. 102(e) as being anticipated by Noguchi et al (US 6,762,564).

Regarding claim 1, Noguchi disclose an active organic light emitting diode, comprising: an organic light emitting diode; a data-line; a scan-line; a switch thin film transistor having a first gate terminal, a first source terminal, a first drain terminal and a first lightly doped drain region, wherein the first gate terminal is coupled to the scan-line and the first source terminal is coupled to the data-line; a control thin film transistor having a second gate terminal, a second source terminal, a second drain terminal and a

second lightly doped drain region, wherein the second drain terminal is coupled to the organic light emitting diode and the first lightly doped drain region and the second lightly doped drain region have different doped concentrations; and a capacitor coupled to the first drain terminal and to the second gate terminal. See figures 1-3, col.1, lines [0018] to col.4, lines [0049].

Regarding claim 2, Noguchi disclose the doped concentration of the second lightly doped drain terminal is higher than that of the first lightly doped drain region. See figures 2-3.

Regarding claims 3-6, Noguchi disclose the switch thin transistor is a P-type low-temperature poly-silicon thin film transistor. See figure 3, col.3, lines [0032] to [0034].

Regarding claim 7, Noguchi disclose an active organic light emitting diode, comprising: an organic light emitting diode; a data-line; a scan-line; a switch thin film transistor having a first gate terminal, a first source terminal, a first drain terminal and a first lightly doped drain region, wherein the first gate terminal is coupled to the scan-line and the first drain terminal is coupled to the data-line; a control thin film transistor having a second gate terminal, a second source terminal, a second drain terminal and a second lightly doped drain region, wherein the second gate terminal is coupled to the first source terminal, the second drain terminal is coupled to the organic light emitting diode and the first lightly doped drain region and the second lightly doped drain region have different lengths; and a capacitor coupled to the first drain terminal and to the second gate terminal. See figures 1-3, col.1, lines [0018] to col.4, lines [0049].

Regarding claim 8, Noguchi disclose the first lightly doped drain terminal is longer than the second lightly doped drain region. See figures 2-3.

Regarding claims 9-12, Noguchi disclose the switch thin film transistor is a P-type low-temperature poly-silicon thin film transistor. See figure 3, col.3, lines [0032] to [0034].

Regarding claim 13, Noguchi disclose an active organic light emitting diode, comprising: an organic light emitting diode; a data-line; a scan-line; a switch thin film transistor having a first gate terminal, a first source terminal, a first drain terminal and a first lightly doped drain region, wherein the first gate terminal is coupled to the scan line and the first drain terminal is coupled to the data-line; a control thin film transistor having a second gate terminal, a second source terminal and a second drain terminal, wherein the second gate terminal is coupled to the first source terminal and the second drain terminal is coupled to the organic light emitting diode; a capacitor coupled to the first drain terminal and to the second gate terminal. See figures 1-3, col.1, lines [0018] to col.4, lines [0049].

Regarding claims 14-17, Noguchi disclose the switch thin film transistor is a P-type low-temperature poly-silicon thin film transistor. See figures 1-3, col.col.3, lines [0032] to [0034].

### ***Conclusion***

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Yamazaki et al (US 6,747,638) and Anza. (US 6,798,405) are cited to show a thin film transistor.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Examiner Minh A whose telephone number is (571) 2721817. The examiner can normally be reached on M-F (5:30 -2:30 PM). If attempts to reach the examiner by telephone is unsuccessful, the examiner's supervisor, Don Wong, can be reached on (571) 272-1834. The fax phone numbers for the organization where this application or proceeding is assigned are 703-872-9306 for regular communications and (703) 872-9319 for final communications.

Any inquiry of a general nature or relating to the status of this application should be directed to the Technology Center receptionist whose telephone number is (571) 272-1553.



**WILSON LEE**  
**PRIMARY EXAMINER**

Examine: Minh A

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8/20/05